

N-channel TrenchMOS standard level FET 11 September 2012

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in a SOT226 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant •
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C •

1.3 Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control •
- Start-Stop micro-hybrid applications •
- Transmission control
- Ultra high performance power switching •

1.4 Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	293	W
Static charac	teristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	1.95	2.3	mΩ
Dynamic cha	racteristics	·	1				
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14		-	33.4	-	nC

[1] Continuous current is limited by package.

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2. Pinning information

Table 2.	Fable 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	G	gate	mb	D				
2	D	drain						
3	S	source		G C C				
mb	D	mounting base; connected to drain	1 2 3 12PAK (SOT226)	mbb076 S				

3. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK7E2R3-40E	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226			

4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7E2R3-40E	BUK7E2R3-40E

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	120	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	1035	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	293	W
T _{stg}	storage temperature			-55	175	°C

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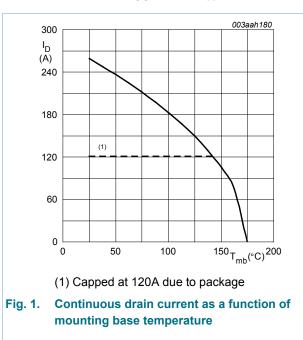
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Symbol	Parameter	Conditions		Min	Мах	Unit
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	1035	А
Avalanche r	ruggedness					_
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 120 \text{ A}; V_{sup} \leq 40 \text{V}; \text{R}_{GS} = 50 \Omega; \\ $	[<u>2][3]</u>	-	622	mJ

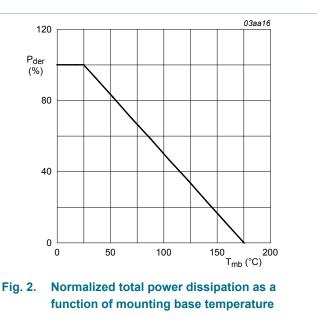
[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.



 $V_{GS} \ge 10V$



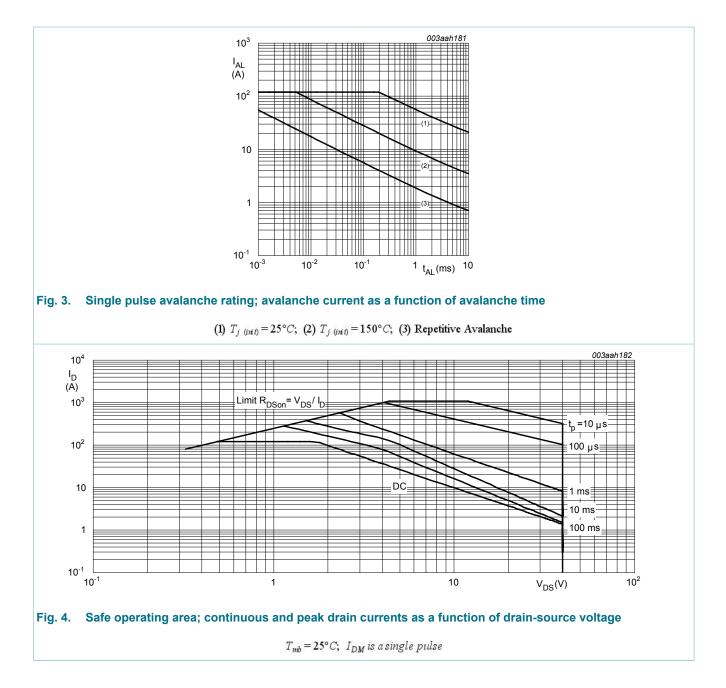
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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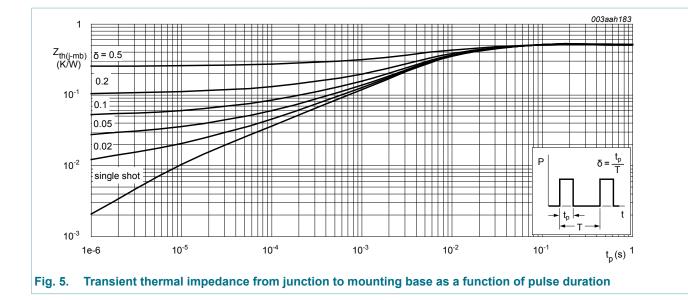


Thermal characteristics 6.

Table 6. Th	nermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.51	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vetical in still air	-	65	-	K/W
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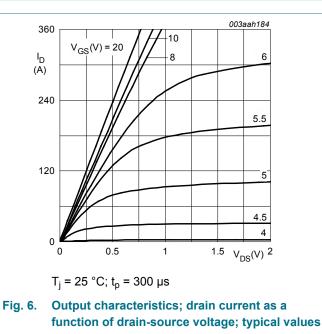


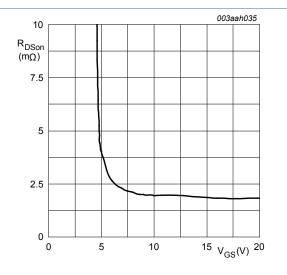
Characteristics 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10	1	-	-	V
l _{DSS} dra	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-	0.36	3	μA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.95	2.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	4.4	mΩ
Dynamic ch	naracteristics		ł			
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V;	-	109.2	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	27.5	-	nC
Q _{GD}	gate-drain charge	1	-	33.4	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	6250	8500	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	 -	1210	1450	pF
C _{rss}	reverse transfer capacitance		-	605	840	pF
t _{d(on)}	turn-on delay time	V_{DS} = 30 V; R _L = 1.2 Ω; V _{GS} = 10 V;	-	29	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	36	-	ns
t _{d(off)}	turn-off delay time		-	79	-	ns
t _f	fall time		-	46	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L _S	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode	I		1		,
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	I_{S} = 20 A; dI_{S}/dt = -100 A/µs; V _{GS} = 0 V;	-	43	-	ns
Q _r	recovered charge	V _{DS} = 25 V	 -	54	-	nC



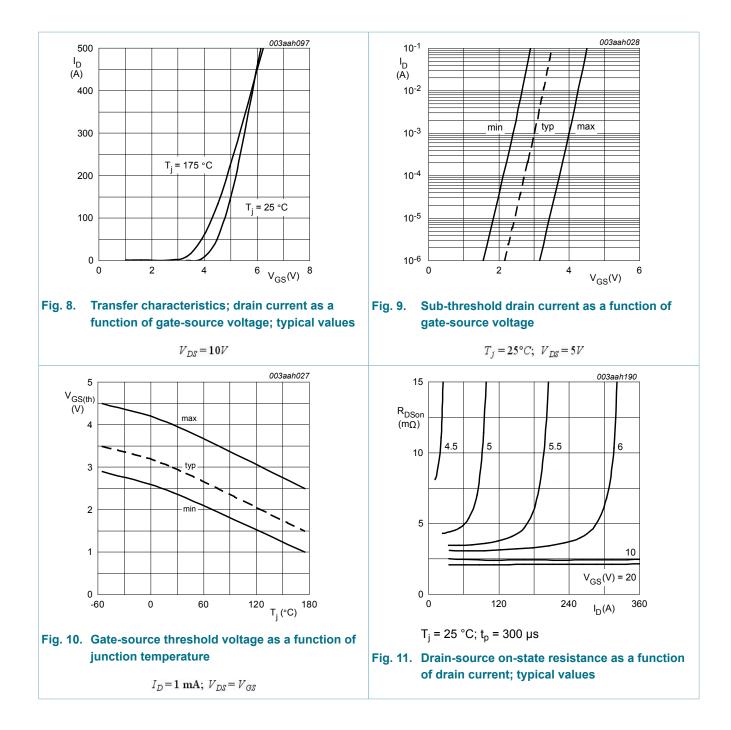




 $T_j = 25^{\circ}C; \ I_D = 25A$

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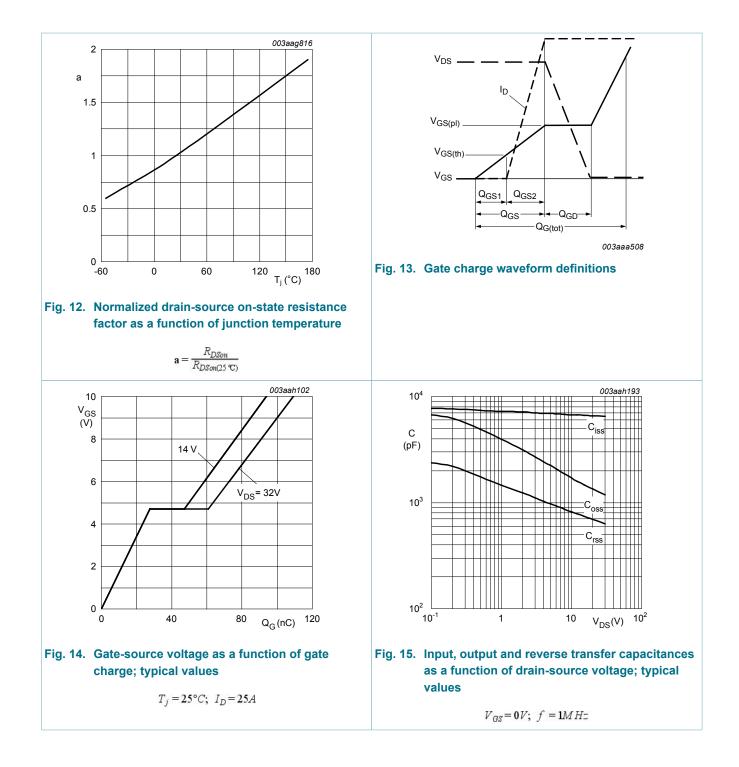
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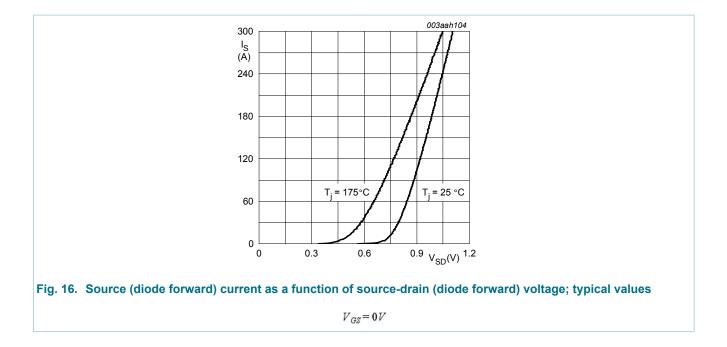
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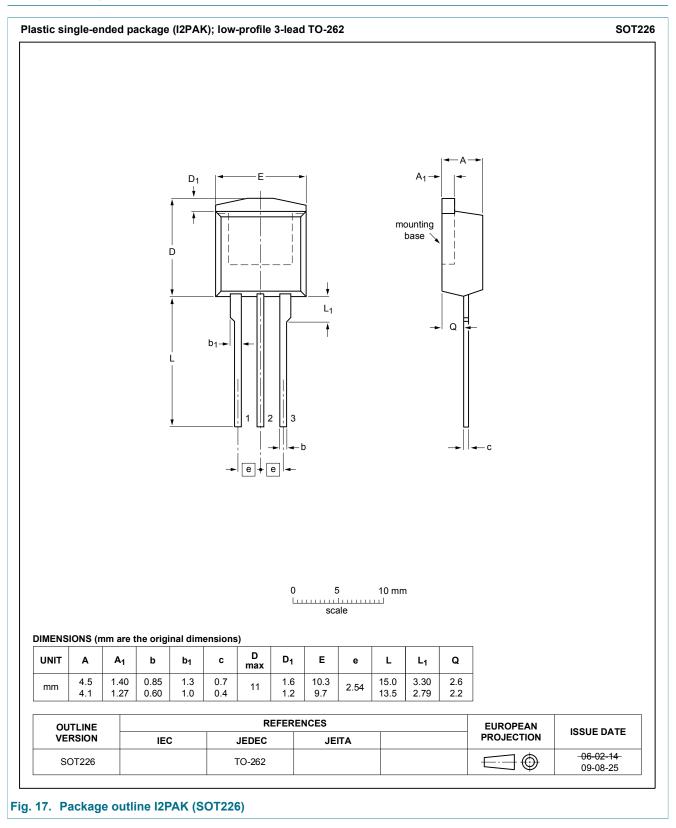
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8. Package outline



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9. Legal information

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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